



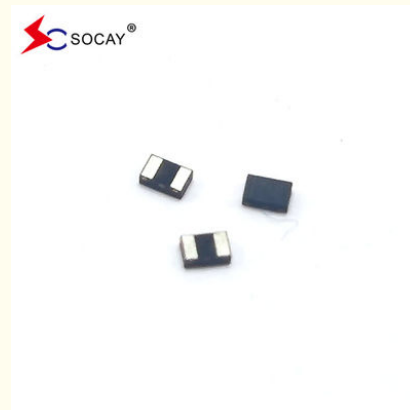
SE03N6L01GZ ESD Array Low Capacitance ESD Protection Operating Voltage 3.3V

Our Product Introduction

for more products please visit us on socaydiode.com

Basic Information

- Place of Origin: Shenzhen Guangdong China
- Brand Name: SOCAY
- Certification: REACH RoHS ISO
- Model Number: SE03N6L01GZ
- Minimum Order Quantity: 10000PCS
- Price: Negotiable
- Delivery Time: 5-8 work days

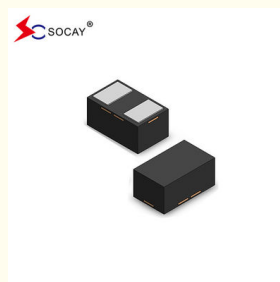
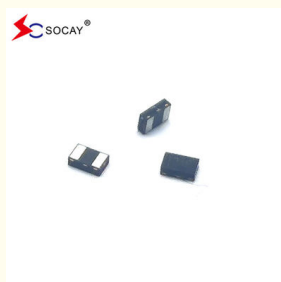


Product Specification

- Component Name: ESD Arrays
- Component Package: DFN1006-2L
- V_{rwm} (Max.): 3.3V
- V_{br} (Min.): 5.0V
- V_{br} (Max.): 6.5V
- I_t : 1mA
- I_r (Max.): 1.0 μ A
- V_c (Typ.) ($I_{pp}=1A$): 9.0V
- V_c (Typ.) ($I_{pp}=5A$): 19.0V
- C_j (Typ.): 0.4pF
- Highlight: ESD Array 3.3V, Low Capacitance ESD Array, Low Capacitance ESD Protection



More Images



Product Description

Low Capacitance ESD Arrays for ESD Protection SE03N6L01GZ Operating Voltage 3.3V

ESD Arrays DATASHEET: [SE03N6L01GZ_v2204.1.pdf](#)

ESD Arrays Features:

Operating Voltage: 3.3V
Low Leakage: nA Level
Low Capacitance
Extremely-Low Clamping Voltage
RoHS compliant

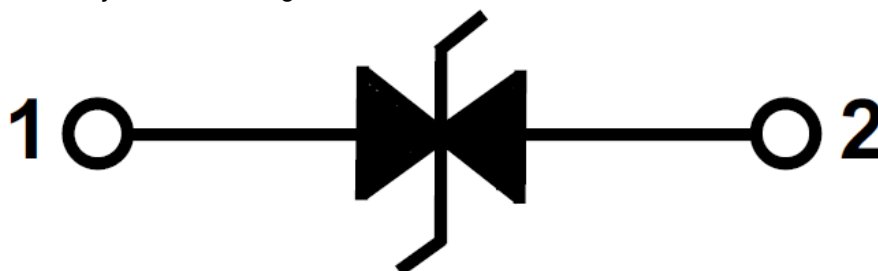
ESD Arrays Applications:

Cellular Handsets & Accessories
Digital Visual Interface (DVI)
RF Circuits
Display Port
USB Ports
MDDI Ports
PCI Express

ESD Arrays Mechanical Characteristics:

DFN1006 (1.0x0.6x0.5mm) Package
Weight 0.5 Milligrams (Approximate)
Quantity Per Reel : 10,000pcs
Reel Size : 7 inch
Lead Finish : Lead Free

ESD Arrays Functional Diagram:



ESD Arrays Absolute Maximum Ratings ($T_A=25$ unless otherwise specified):

Symbol	Parameter	Value	Units
T_L	Lead Soldering Temperature	260 (10sec)	$^{\circ}\text{C}$
T_{OP}	Operating Temperature Range	-55 to +125	
T_{STG}	Storage Temperature Range	-55 to +150	
V_{ESD}	ESD per IEC61000-4-2 (Air)	± 25	kV
	ESD per IEC61000-4-2 (Contact)	± 25	

Electrical Characteristics ($T_A = 25$ unless otherwise specified):

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Reverse Working Voltage	VRWM	--	--	--	3.3	V
Breakdown Voltage	VBR	$I_T = 1\text{mA}$	5.0	--	6.5	V
Leakage Current	IR	VRWM = 3.3V	--	--	1.0	μA
Clamping Voltage	VC	IPP = 1A, $t_P = 8/20\mu\text{s}$	--	9.0	--	V
Clamping Voltage	VC	IPP = 5A, $t_P = 8/20\mu\text{s}$	--	19.0	--	V
Junction Capacitance	CJ	VR = 0V, f = 1MHz	--	0.4	--	pF

ESD Arrays Characteristic Curves:

Fig1. 8/20 us Pulse Waveform

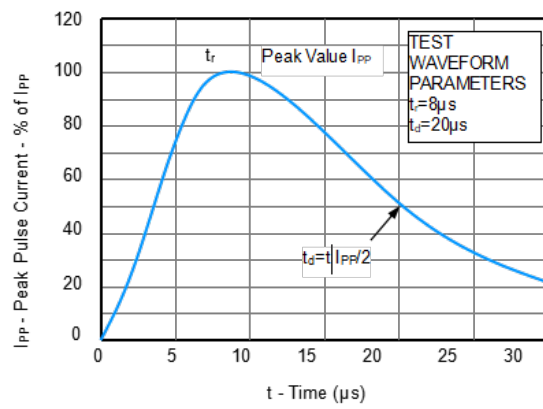
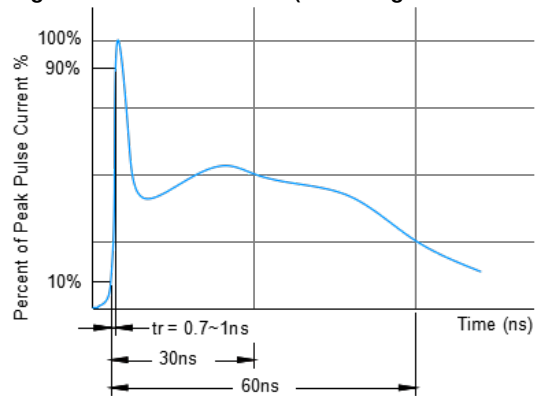


Fig2. ESD Pulse Waveform (according to IEC 61000-4-2)



DFN1006-2L Package Outline & Dimensions:

Symbol	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.450	0.550	0.018	0.022
A1	0.010	0.070	0.000	0.003
D	0.950	1.050	0.037	0.041
E	0.550	0.650	0.022	0.026
D1	0.450 REF		0.018 REF	
E1	0.400 REF		0.016 REF	
b	0.275	0.325	0.011	0.013
e	0.675	0.725	0.027	0.029
L	0.275	0.325	0.011	0.013
L1	0.010 REF		0.000 REF	

